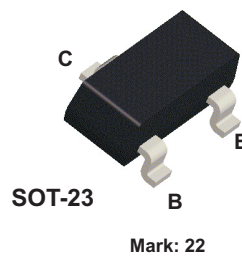


## MMBT4209



### PNP General Purpose Amplifier

This device is designed as a general purpose amplifier and switch. The useful dynamic range extends to 10 mA as a switch and to 850 MHz as an amplifier.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	15	V
$V_{CBO}$	Collector-Base Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current - Continuous	10	mA
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

**Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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**OFF CHARACTERISTICS**

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	15		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E$	20		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V

**ON CHARACTERISTICS\***

$h_{FE}$	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	50		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1 \text{ mA}, I_B = 100 \text{ mA}$ $I_C = 5 \text{ mA}, I_B = 0.5 \text{ mA}$		0.2 0.3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1 \text{ mA}, I_B = 100 \text{ mA}$ $I_C = 5 \text{ mA}, I_B = 0.5 \text{ mA}$	0.65	0.85 0.95	V V

**SMALL SIGNAL CHARACTERISTICS**

$f_T$	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$	850		Mhz
$C_{obo}$	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ $f = 1.0 \text{ MHz}$		2.0	pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_C = 0,$ $f = 1.0 \text{ MHz}$		3.0	pF

**SWITCHING CHARACTERISTICS**

$t_r$	Rise Time	$I_C = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA}$		35	ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$		50	ns

**Spice Model**